

5 a gate insulation film formed on a lower portion of the active layer and a
6 sidewall^{portion} of the active layer contiguous the lower portion of the active layer and^{the}
7 sidewall of the stepped substrate, respectively;

fig. 2 8 an insulating film formed on a lower portion of the gate insulation film
9 and a sidewall^{portion} of the gate [insulating] film contiguous the lower portion of the
10 gate [insulating] film and^{the} sidewall of the [stepped substrate], respectively;

D' a gate electrode formed on the gate insulation film corresponding to the
12 sidewalls of the substrate and the [insulating] film;

impurity regions in the active layer corresponding to the upper and lower
portions of the substrate; and

15 an offset region formed [on the whole lower region of the sidewall and
16 substrate corresponding to the insulating film as a single region].

D² 1 5. (Amended) The thin film transistor of claim 1, wherein the [insulating]
film is a spin-on-glass film.

REMARKS

Claims 1, 2, and 4-6 remain in this application.

Claims 1 and 5 have been amended to overcome the Section 112,
paragraph 2 rejection in accordance with the Examiner's helpful suggestions.